

## ATTACHMENT B Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) An etching solution having a thermal oxide (THOX) film etch rate and boron phosphosilicate glass (BPSG) film etch rate at 25°C of 100Å/min or lower and a ratio of (BPSG etch rate) / (THOX etch rate) of 1.5 or lower, wherein the solution comprises (i) at least one member selected from the group consisting of a fluoride salt and a hydrogenfluoride salt; and (ii) solvent being at least one member selected from organic solvents, organic acids and water, and wherein said organic acids are selected from the group consisting of essentially of acetic acid, propionic acid, butyric acid, isobutyric acid, valeric acid, caproic acid, caprylic acid, monochloroacetic acid, dichloroacetic acid, trichloroacetic acid, monofluoroacetic acid, difluoroacetic acid, trifluoroacetic acid, α-chlorobutyric acid, β-chlorobutyric acid, γ-chlorobutyric acid, lactic acid, glycolic acid, pyruvic acid, glyoxalic acid, acrylic acid, and like monocarboxylic acids methanesulfonic acid and toluenesulfonic acid.
2. (Original) The etching solution according to claim 1 comprising at least one member selected from the group consisting of a fluoride salt and a bifluoride salt.

3. (Original) The etching solution according to claim 1, wherein a solvent of the etching solution has a relative dielectric constant of 35 or lower.

4. (Previously Presented) The etching solution according to claim 1 comprising at least one member selected from the group consisting of an organic acid and an organic solvent comprising molecules having a hetero atom.

5. (Previously Presented) The etching solution according to claim 1 comprising (i) ammonium hydrogen fluoride, (ii) water and (iii) at least one member selected from the group consisting of an organic acid and an organic solvent comprising molecules having a hetero atom, the water being contained in a concentration of 3% by weight or lower.

6. (Previously Presented) The etching solution according to claim 1 comprising ammonium hydrogen fluoride, water and isopropyl alcohol, the water being contained in a concentration of 3% by weight or lower.

7. (Previously Presented) The etching solution according to claim 1 comprising ammonium hydrogen fluoride, water and ethanol, the water being contained in a concentration of 3% by weight or lower.

8. (Previously Presented) The etching solution according to claim 1 comprising ammonium hydrogen fluoride, water and acetone, the water being contained in a concentration of 3% by weight or lower.

9. (Previously Presented) The etching solution according to claim 1 comprising (i) ammonium fluoride and (ii) at least one member selected from the group consisting of an organic acid and an organic solvent comprising molecules having a hetero atom.

10. (Previously Presented) The etching solution according to claim 1 comprising (i) ammonium fluoride, (ii) water and (iii) at least one member selected from the group consisting of an organic acid and an organic solvent comprising molecules having a hetero atom, the water being contained in a concentration of 10% by weight or lower.

11. (Original) The etching solution according to claim 1 comprising ammonium fluoride, water and ethanol, the water being contained in a concentration of 10% by weight or lower.

12. (Original) The etching solution according to claim 1 comprising ammonium fluoride, water and isopropyl alcohol, the water being contained in a concentration of 10% by weight or lower.

13. (Original) The etching solution according to claim 1 comprising ammonium fluoride, water and acetic acid, the water being contained in a concentration of 1.5% by weight or lower.

14. (Withdrawn) A method for producing an etched article by etching an article with the etching solution as defined in claim 1.

15. (Withdrawn) An etched article which is produced by the method of claim 14.

16. (Previously presented) An etching solution having a thermal oxide (THOX) film etch rate and boron phosphosilicate glass (BPSG) film etch rate at 25°C of 100Å/min or lower and a ratio of (BPSG etch rate) / (THOX etch rate) of 1.5 or lower, said etching solution comprising ammonium fluoride, water and acetic acid, the water being contained in a concentration of 1.5% by weight or lower.